

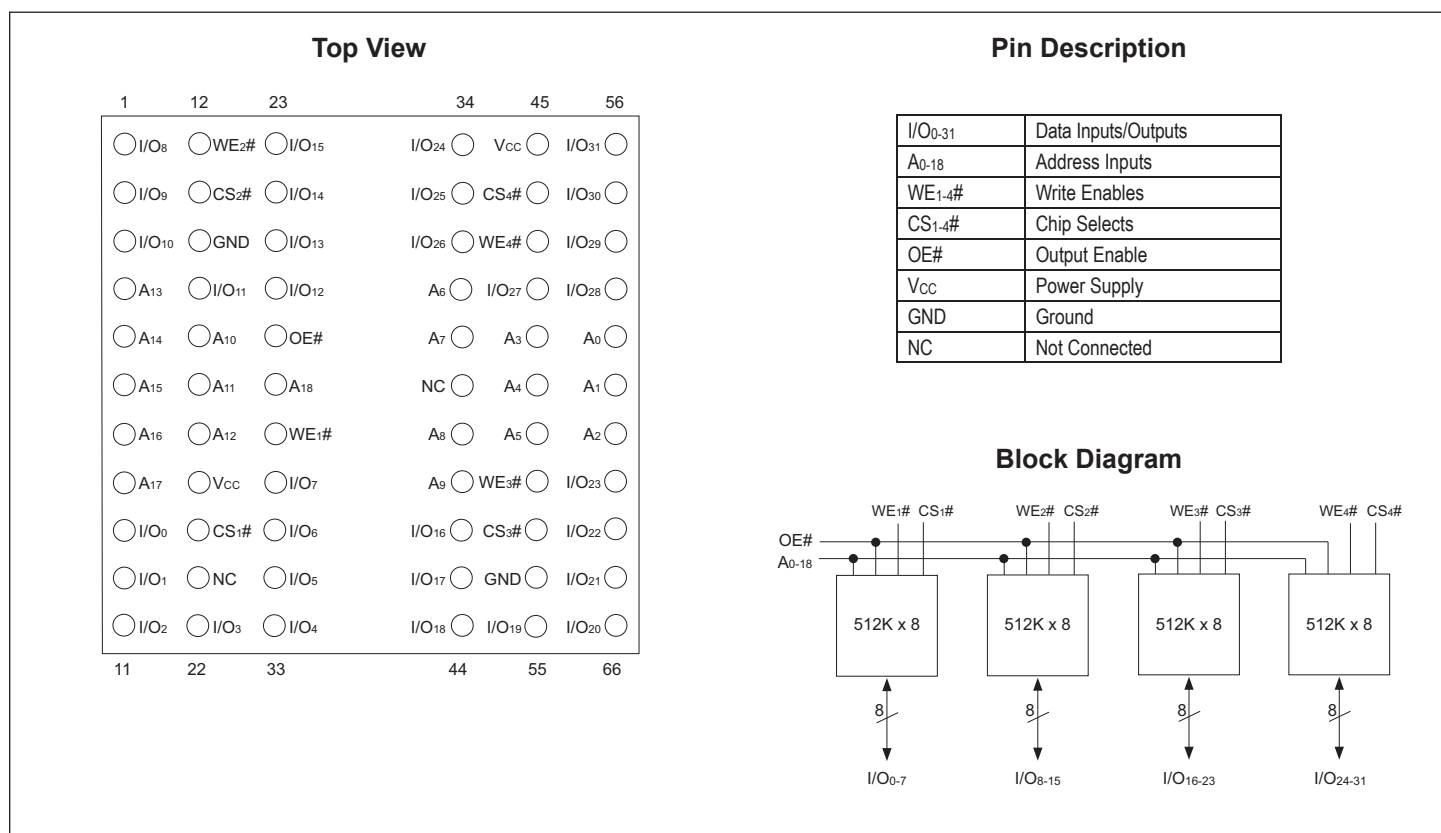
512Kx32 SRAM 3.3V MULTICHIP PACKAGE

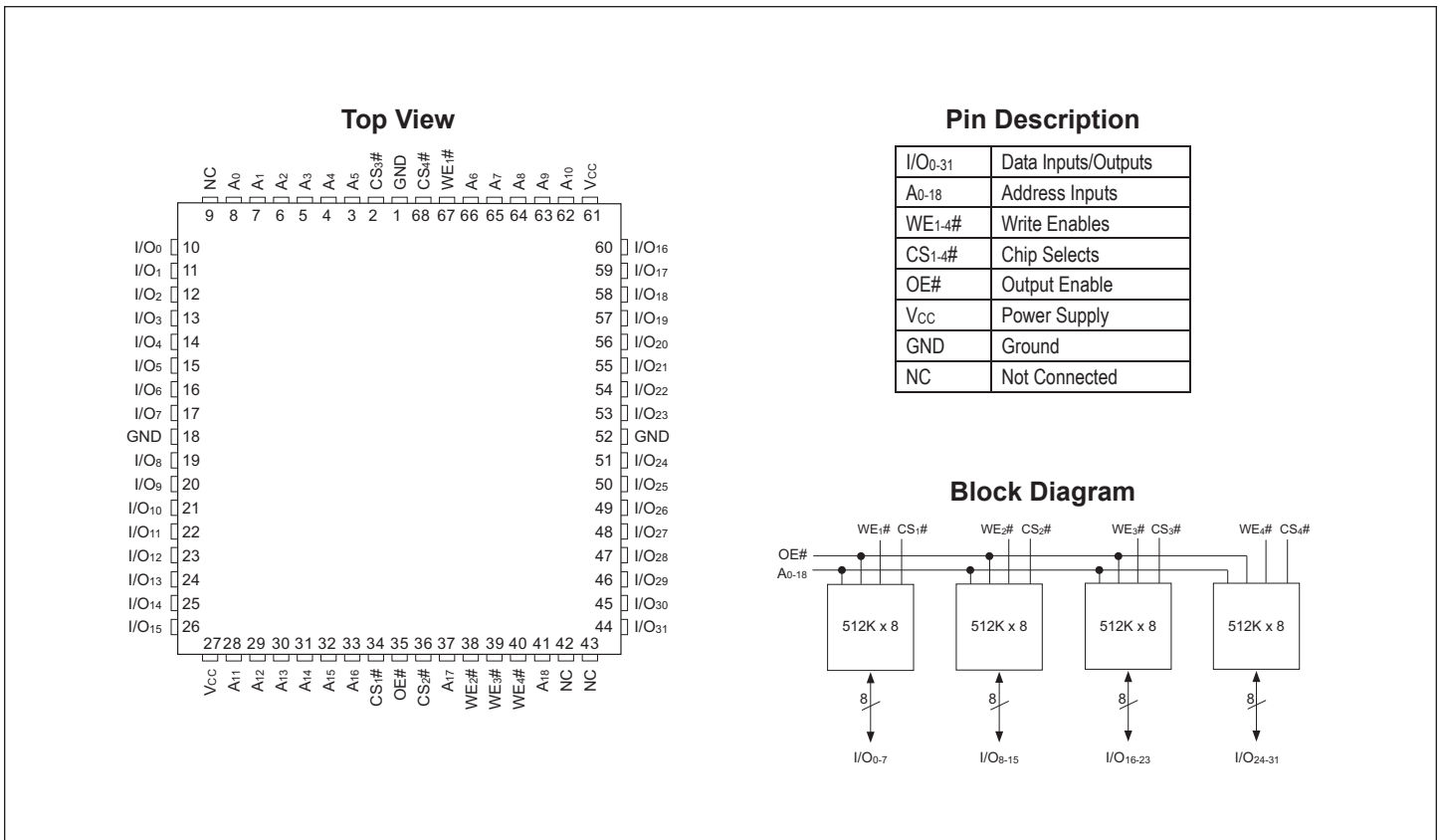
FEATURES

- Access Times of 15, 17, 20ns
- Low Voltage Operation
- Packaging
 - 66-pin, PGA Type, 1.075 inch square, Hermetic Ceramic HIP (Package 400)
 - 8 lead, 22.4mm (0.880 inch) CQFP, (G2U), 3.56mm (0.140"), (Package 510)
- Organized as 512Kx32; User Configurable as 2x512Kx16 or 4x512Kx8
- Commercial, Industrial and Military Temperature Ranges
- Low Voltage Operation:
 - 3.3V ± 10% Power Supply
- Low Power CMOS
- TTL Compatible Inputs and Outputs
- Fully Static Operation:
 - No clock or refresh required.
- Three State Output.
- Built-in Decoupling Caps and Multiple Ground Pins for Low Noise Operation
- Weight
 - WS512K32V-XG2UX - 8 grams typical
 - WS512K32NV-XH1X - 13 grams typical

* This product is subject to change without notice.

PIN CONFIGURATION FOR WS512K32NV-XH1X



PIN CONFIGURATION FOR WS512K32V-XG2UX


ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-55	+125	°C
Storage Temperature	T _{STG}	-65	+150	°C
Signal Voltage Relative to GND	V _G	-0.5	4.6	V
Junction Temperature	T _J		150	°C
Supply Voltage	V _{CC}	-0.5	4.6	V

TRUTH TABLE

CS	OE	WE	Mode	Data I/O	Power
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	X	L	Write	Data In	Active
L	H	H	Out Disable	High Z	Active

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	3.0	3.6	V
Input High Voltage	V _{IH}	2.2	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.3	+0.8	V

CAPACITANCE

 T_A = +25°C

Parameter	Symbol	Conditions	Max	Unit
OE# capacitance	C _{OE}	V _{IN} = 0V, f = 1.0 MHz	50	pF
WE ₁₋₄ # capacitance HIP (PGA)	C _{WE}	V _{IN} = 0V, f = 1.0 MHz	20	pF
CQFP G2U			20	
CS ₁₋₄ # capacitance	C _{CS}	V _{IN} = 0V, f = 1.0 MHz	20	pF
Data# I/O capacitance	C _{I/O}	V _{I/O} = 0V, f = 1.0 MHz	20	pF
Address input capacitance	C _{AD}	V _{IN} = 0V, f = 1.0 MHz	50	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

 V_{CC} = 3.3V ± 0.3V, V_{SS} = 0V, -55°C ≤ T_A ≤ +125°C

Parameter	Symbol	Conditions			Units
			Min	Max	
Input Leakage Current	I _{LI}	V _{IN} = GND to V _{CC}		10	μA
Output Leakage Current	I _{LO}	CS# = V _{IH} , OE# = V _{IH} , V _{OUT} = GND to V _{CC}		10	μA
Operating Supply Current	I _{CC} x 32	CS# = V _{IL} , OE# = V _{IH} , f = 5MHz, V _{CC} = 3.6		400	mA
Standby Current	I _{SB}	CS# = V _{IH} , OE# = V _{IH} , f = 5MHz, V _{CC} = 3.6		200	mA
Output Low Voltage	V _{OL}	I _{OL} = 4.0mA		0.4	V
Output High Voltage	V _{OH}	I _{OH} = -4.0mA	2.4		V

 NOTE: DC test conditions: V_{IH} = V_{CC} - 0.3V, V_{IL} = 0.3V.

Contact factory for low power option.

AC CHARACTERISTICS
 $V_{CC} = 3.3V, GND = 0V, -55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol	-15		-17		-20		Units
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{RC}	15		17		20		ns
Address Access Time	t _{AA}		15		17		20	ns
Output Hold from Address Change	t _{OH}	0		0		0		ns
Chip Select Access Time	t _{ACS}		15		17		20	ns
Output Enable to Output Valid	t _{OE}		8		8		10	ns
Chip Select to Output in Low Z	t _{CLZ} ¹	1		1		1		ns
Output Enable to Output in Low Z	t _{OLZ} ¹	0		0		0		ns
Chip Disable to Output in High Z	t _{CHZ} ¹		8		8		10	ns
Output Disable to Output in High Z	t _{OHZ} ¹		8		8		10	ns

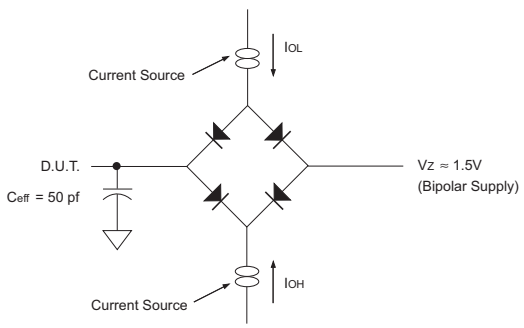
1. This parameter is guaranteed by design but not tested.

AC CHARACTERISTICS
 $V_{CC} = 3.3V, GND = 0V, -55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol	-15		-17		-20		Units
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{WC}	15		17		20		ns
Chip Select to End of Write	t _{CW}	12		12		14		ns
Address Valid to End of Write	t _{AW}	12		12		14		ns
Data Valid to End of Write	t _{DW}	9		9		10		ns
Write Pulse Width	t _{WP}	12		14		14		ns
Address Setup Time	t _{AS}	0		0		0		ns
Address Hold Time	t _{AH}	0		0		0		ns
Output Active from End of Write	t _{OW} ¹	2		3		3		ns
Write Enable to Output in High Z	t _{WHZ} ¹		8		8		9	ns
Data Hold Time	t _{DH}	0		0		0		ns

1. This parameter is guaranteed by design but not tested.

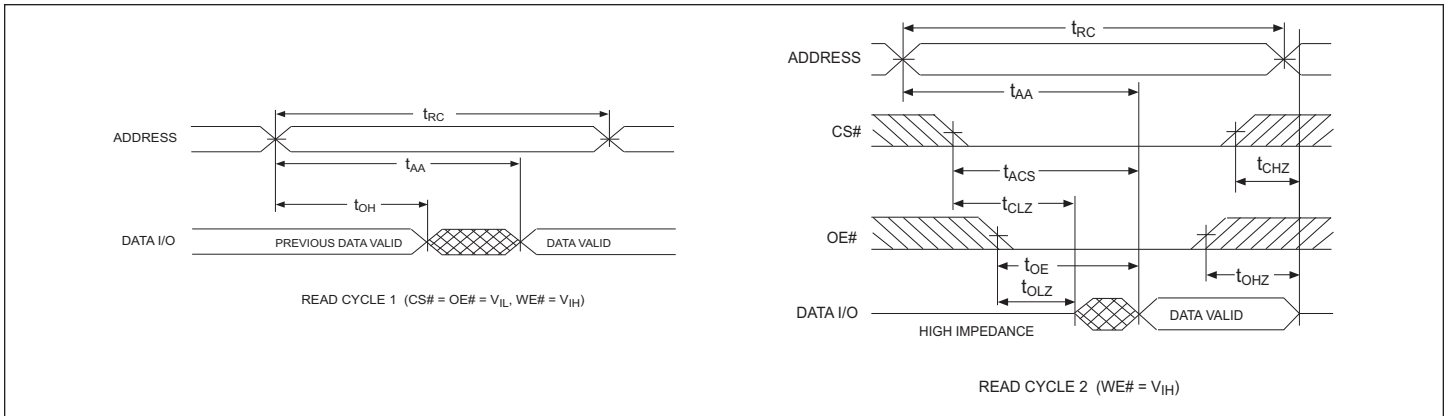
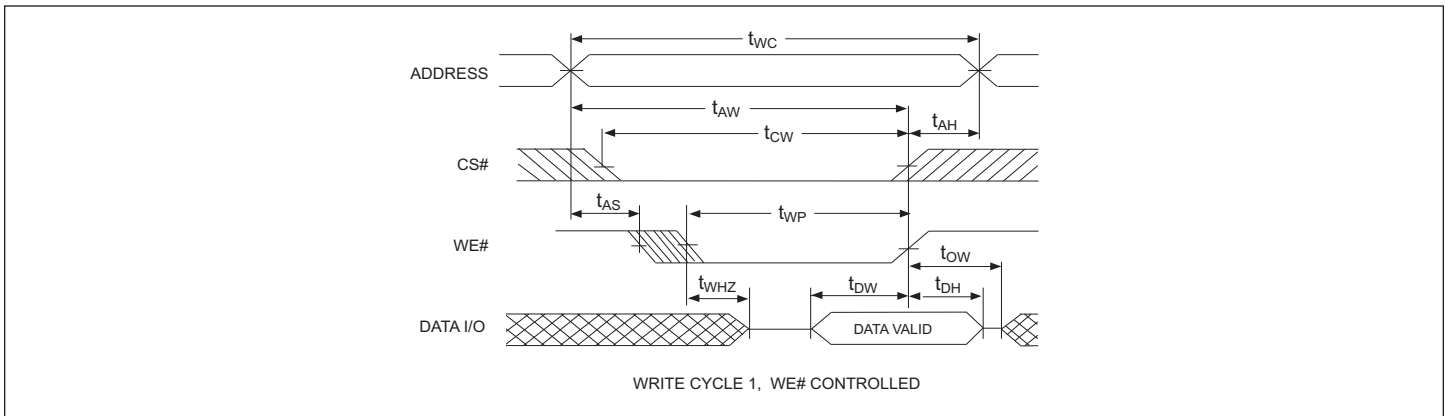
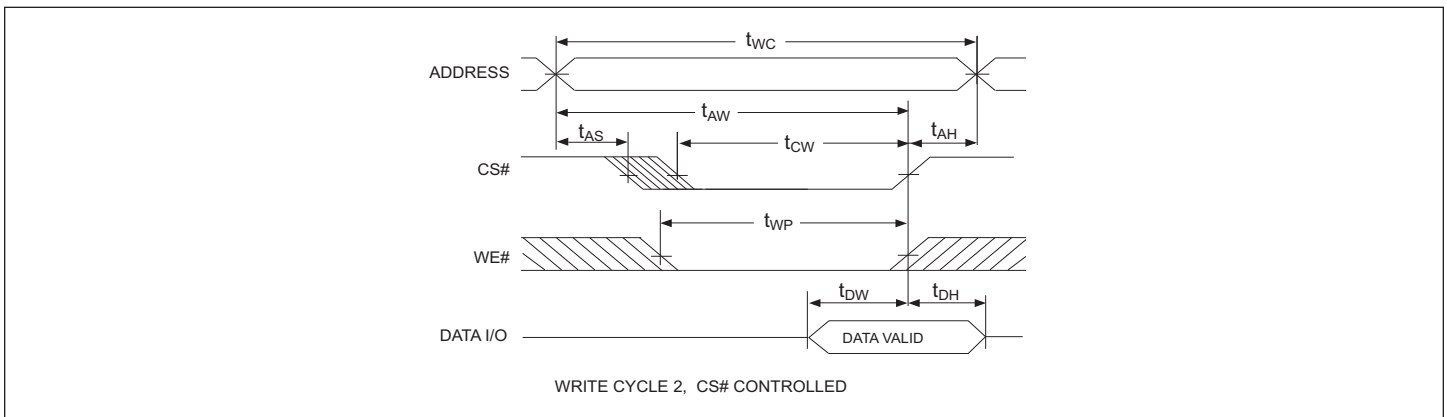
AC TEST CIRCUIT

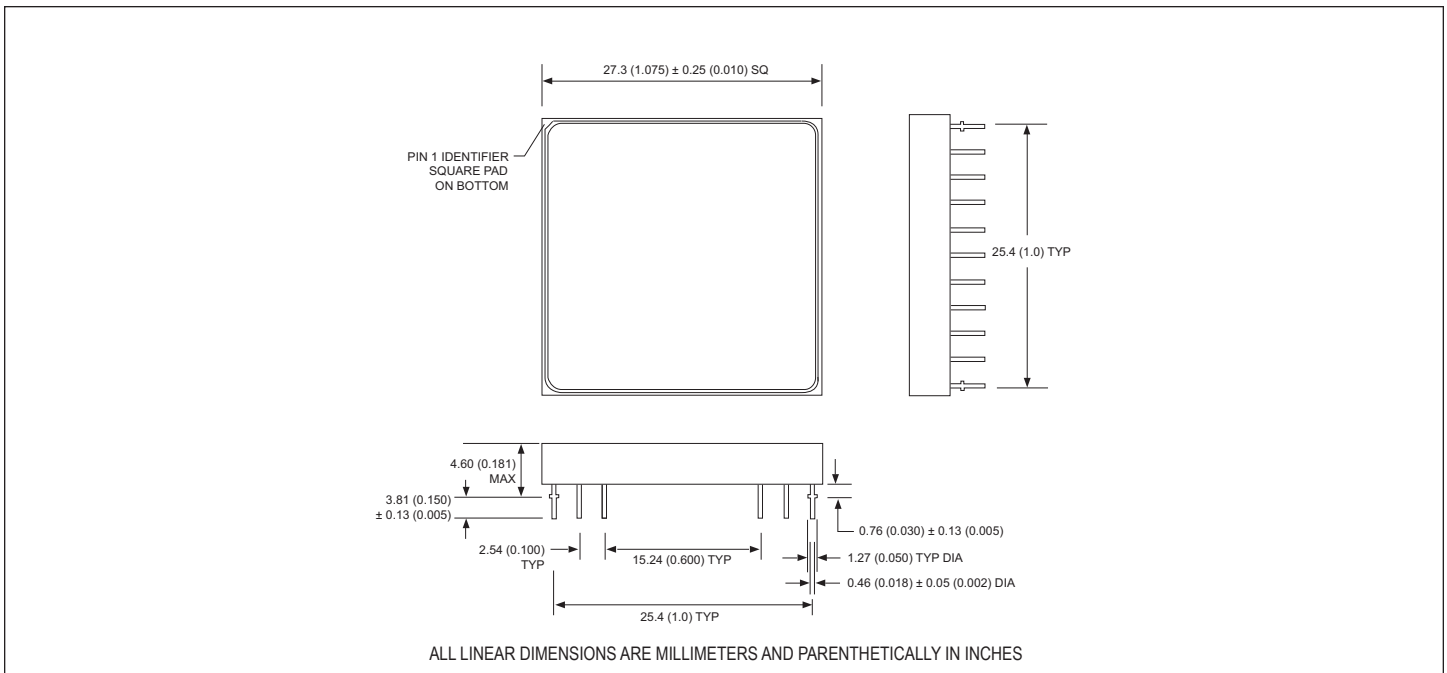
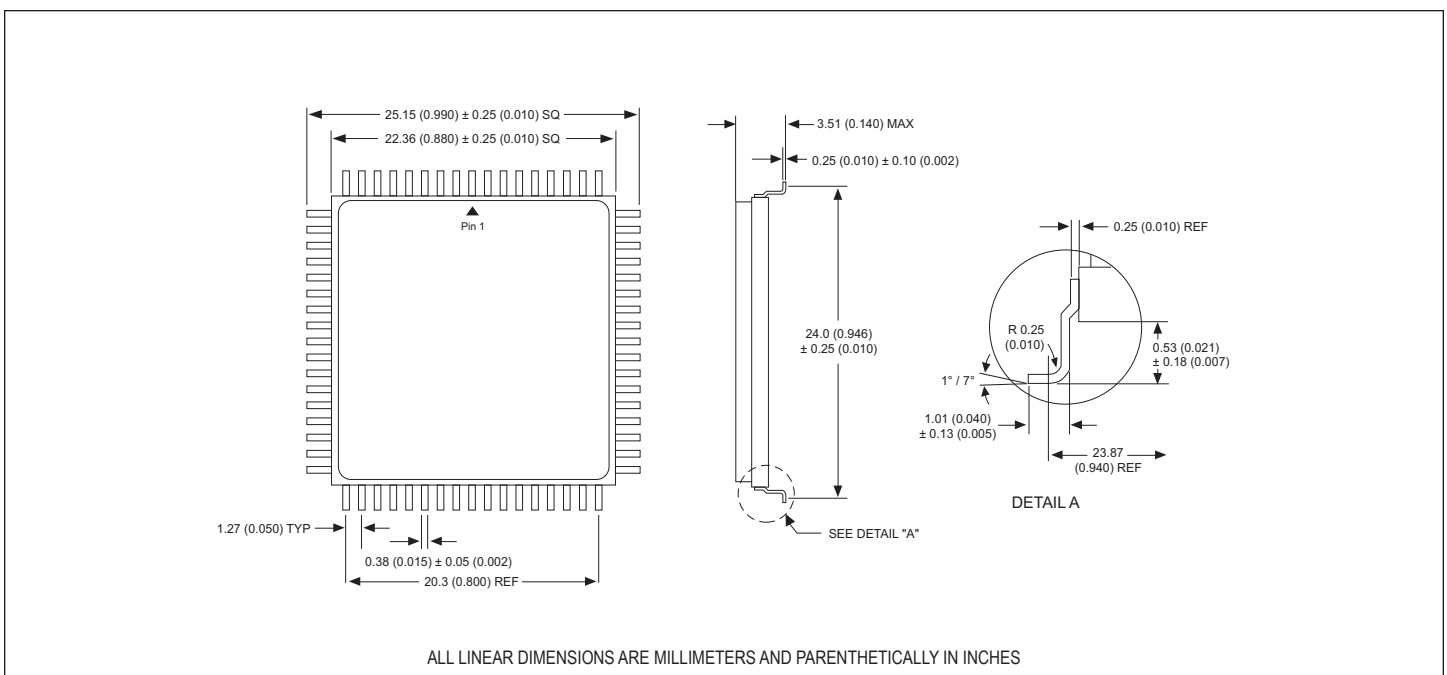


The diagram shows a Device Under Test (D.U.T.) connected to a bipolar supply. The supply is represented by two current sources, one for the load (I_{OL}) and one for the output (I_{OH}). The supply voltage is V_Z ≈ 1.5V. A capacitor C_{eff} = 50 pf is connected to the D.U.T. input. The load is represented by a resistor.

AC Test Conditions		
Parameter	Typ	Unit
Input Pulse Levels	V _{IL} = 0, V _{IH} = 2.5	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

Notes:
 V_Z is programmable from -2V to +7V.
 I_{OL} & I_{OH} programmable from 0 to 16mA.
 Tester Impedance Z₀ = 75 Ω.
 V_Z is typically the midpoint of V_{OH} and V_{OL}.
 I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.
 ATE tester includes jig capacitance.

TIMING WAVEFORM – READ CYCLE

WRITE CYCLE – WE# CONTROLLED

WRITE CYCLE – CS# CONTROLLED


PACKAGE 400: 66 PIN, PGA TYPE, CERAMIC HEX-IN-LINE PACKAGE, HIP (H1)

PACKAGE 510: 68 LEAD, LOW PROFILE CERAMIC QUAD FLAT PACK, CQFP (G2U)




ORDERING INFORMATION

W S 512K 32 X V - XXX X X X

MICROSEMI CORPORATION _____

SRAM _____

ORGANIZATION, 512Kx32 _____

User configurable as 2x512Kx16 or 4x512Kx8

IMPROVEMENT MARK: _____

N = No Connect at pin 21 and 39 in HIP for Upgrades (H1 only)

Low Voltage Supply 3.3V ± 10% _____

ACCESS TIME (ns) _____

PACKAGE TYPE: _____

H1 = 1.075" sq. Ceramic Hex In Line Package, HIP (Package 400)
G2U = 22.4mm Ceramic Quad Flat Pack, CQFP (Package 510)

DEVICE GRADE: _____

M = Military -55°C to +125°C
I = Industrial -40°C to +85°C
C = Commercial 0°C to +70°C

LEAD FINISH: _____

Blank = Gold plated leads
A = Solder dip leads